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Cancel Claim 9, without prejudice.

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10. (Amended) The FET of claim 11, wherein said first conductive material is on a gate dielectric and said gate dielectric is on a substrate.

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11. (Amended) An FET comprising a gate, said gate comprising a first conductive material and a second conductive material different from said first conductive material, said second conductive material being disposed on said first conductive material, wherein said second conductive material extends beyond said first conductive material to provide a T-shaped gate, and wherein said first material has a dimension less than a photolithographic minimum dimension.

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12. (Amended) The FET of claim 11, wherein said first material comprises a first semiconductor material.

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15. (Amended) The FET of claim 11, wherein said second conductive material comprises polysilicon.

16. (Amended) The FET of claim 11, wherein said first conductive material comprises polysilicon.

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19. (Amended) The FET of claim 11, wherein said second conductive material comprises a silicide.

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20. (Amended) The FET of claim 11, further comprising a spacer along sidewalls of said second conductive material.